1.35 mA

27 kHz

100 mV from rails



LPV511 Micropower, Rail-to-Rail Input and Output Operational Amplifier

General Description

Typical Application

The LPV511 is a micropower operational amplifier that operates from a voltage supply range as wide as 2.7V to 12V with guaranteed specifications at 3V, 5V and 12V. The LPV511 exhibits an excellent speed to power ratio, drawing only 880 nA of supply current with a bandwidth of 27 kHz. These specifications make the LPV511 an ideal choice for battery powered systems that require long life through low supply current, such as instrumentation, sensor conditioning and battery current monitoring.

The LPV511 has an input range that includes both supply rails for ground and high side battery sensing applications. The LPV511 output swings within 100 mV of either rail to maximize the signal's dynamic range in low supply applications. In addition, the output is capable of sourcing 650 μ A of current when powered by a 12V battery.

The LPV511 is fabricated on National's advanced VIP50C process.

The LPV511 is available in the space saving SC70 package which makes it ideal for portable electronics with area constrained PC boards.

Features

(Typical at 3V supply unless otherwise noted)

 Wide supply voltage range 	2.7V to 12V
 Slew rate 	7.7 V/ms
 Supply current 	880 nA

- Output short circuit current
- Rail-to-rail input
- Rail-to-rail output
- Bandwidth ($C_1 = 50 \text{ pF}, R_1 = 1 \text{ M}\Omega$)
- Unity gain stable

Applications

- Battery powered systems
- Security systems
- Micropower thermostats
- Solar powered systems
- Portable instrumentation
- Micropower filter
- Remote sensor amplifier

VOUT

20117003

R, 2k R_{SENSE} 0.2 Q 1 R_2 2N3906 2k ο Load R_3 10k I_{CHARGE} R_{SENSE} V_{OUT} $I_{Charge} = 1 \Omega \cdot I_{Charge}$

High Side Battery Current Sensor

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2)	
Human Body	2 KV
Machine Model	200V
V _{IN} Differential	2.1V
Supply Voltage (V+ - V-)	13.2V
Voltage at Input/Output pins	V+ +0.3V, V ⁻ -0.3V
Storage Temperature Range	–65°C to +150°C
Short Circuit Duration	(Note 4)

Junction Temperature (Note 3) Soldering Information	+150°C
Infrared or Convection (20 sec)	235°C
Wave Soldering Lead Temp. (10 sec)	260°C
Operating Ratings (Note 1)	
Temperature Range (Note 3) Supply Voltage (V+ – V−)	-40°C to +85°C 2.7V to 12V

Package Thermal Resistance (θ_{JA} (Note 3)) 5-Pin SC70 456°C/W

3V Electrical Characteristics (Note 5)

Unless otherwise specified, all limits are guaranteed for $T_J = 25^{\circ}C$, $V^+ = 3V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$, and $R_L = 100 \text{ k}\Omega$ to $V^+/2$. Boldface limits apply to the temperature range of $-40^{\circ}C$ to $85^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 6)	(Note 7)	(Note 6)	
V _{os}	Input Offset Voltage			±0.2	±3 ±3.8	mV
TC V _{os}	Input Offset Voltage Drift	(Note 8)		±0.3	±15	µV/°C
В	Input Bias Current (Note 9)	V _{CM} = 0.5V	-1000 - 1600	-320		
		V _{CM} = 2.5V		110	800 1900	pА
os	Input Offset Current			±10		pА
CMRR	Common Mode Rejection Ratio	ommon Mode Rejection Ratio V _{CM} Stepped from 0V to 1.5V 77 70	100			
		V _{CM} Stepped from 2.4V to 3V	75 68	115		dB
		V_{CM} Stepped from 0.5V to 2.5V	60 56	80		
PSRR	Power Supply Rejection Ratio	$V^+ = 2.7V$ to 5V, $V_{CM} = 0.5V$	72 68	114		dB
		$V^+ = 3V \text{ to } 5V, V_{CM} = 0.5V$	76 72	115		
		V ⁺ = 5V to 12V, $V_{CM} = 0.5V$	84 80	117		
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	-0.1 0		3.1 3.0	V
A _{VOL}	Large Signal Voltage Gain	Sinking, V _O = 2.5V	75	105	1	dB
		Sourcing, V _O = 0.5V	70	105		
Vo	Output Swing High	V _{ID} = 100 mV	2.85 2.8	2.90		V
	Output Swing Low	V _{ID} = -100 mV		100	150 200	mV
SC	Output Short Circuit Current (Note 10)	Sourcing V _{ID} = 100 mV		-500	-225	
		Sinking V _{ID} = -100 mV	225	1350		- μΑ
S	Supply Current			0.88	1.2 1.5	μA
SR	Slew Rate (Note 11)	$A_V = +1$, V_O ramps from 0.5V to 2.5V	5.25 3.10	7.7		V/ms

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 6)	(Note 7)	(Note 6)	
GBW	Gain Bandwidth Product	$R_L = 1 M\Omega, C_L = 50 pF$		27		kHz
	Phase Margin	$R_L = 1 M\Omega, C_L = 50 pF$		53		deg
e _n	Input-Referred Voltage Noise	f = 100 Hz		320		nV/√Hz
i _n	Input-Referred Current Noise	f = 10 Hz		.02		
		f = 1 kHz		.01		pA/√Hz

5V Electrical Characteristics (Note 5)

Unless otherwise specified, all limits are guaranteed for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$, and $R_L = 100 \text{ k}\Omega$ to $V^+/2$. Boldface limits apply to the temperature range of $-40^{\circ}C$ to $85^{\circ}C$.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 7)	Max (Note 6)	Units
V _{OS}	Input Offset Voltage			±0.2	±3 ±3.8	mV
TC V _{os}	Input Offset Voltage Drift	(Note 8)		±0.3	±15	µV/°C
I _B	Input Bias Current (Note 9)	V _{CM} = 0.5V	-1000 - 1600	-320		54
		V _{CM} = 4.5V		110	800 1900	рA
I _{os}	Input Offset Current			±10		pА
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from 0V to 2.5V	80 73	115		
		V_{CM} Stepped from 4.4 to 5V	75 68	107		dB
		V_{CM} Stepped from 0.5 to 4.5V	65 62	87		
PSRR	Power Supply Rejection Ratio	$V^+ = 2.7V$ to 5V, $V_{CM} = 0.5V$	72 68	114		
		$V^{+} = 3V$ to 5V, $V_{CM} = 0.5V$	76 72	115		dB
		$V^{+} = 5V$ to 12V, $V_{CM} = 0.5V$	84 80	117		
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	-0.1 0		5.1 5	V
A _{VOL}	Large Signal Voltage Gain	Sinking, $V_0 = 4.5V$	78			5
		Sourcing, V _O = 0.5V	73	110		dB
Vo	Output Swing High	V _{ID} = 100 mV	4.8 4.75	4.89		V
	Output Swing Low	V _{ID} = -100 mV		110	200 250	mV
I _{SC}	Output Short Circuit Current (Note 10)	Sourcing to V- V _{ID} = 100 mV		-550	-225	
		Sinking to V+ V _{ID} = -100 mV	225	1350		μA
I _S	Supply Current	<u></u>		0.97	1.2 1.5	μA
SR	Slew Rate (Note 11)	$A_V = +1$, V_O ramps from 0.5V to 4.5V	5.25 3.10	7.5		V/ms
GBW	Gain Bandwidth Product	$R_L = 1 M\Omega$, $C_L = 50 pF$		27		kHz
	Phase Margin	$R_{\rm I} = 1 \ M\Omega, \ C_{\rm I} = 50 \ \rm pF$		53		deg
e _n	Input-Referred Voltage Noise	f = 100 Hz		320		nV/√H:

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Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 7)	Max (Note 6)	Units	
i _n	Input-Referred Current Noise	f = 10 Hz		.02			
		f = 1 kHz		.01		рА/√Н	
Unless	Electrical Characteris otherwise specified, all limits are gua the limits apply to the temperature	aranteed for $T_J = 25^{\circ}C$, V ⁺ = 12V, V ⁻ = 0V	/, V _{CM} = V _O =	V+/2, and F	R _L = 100 kΩ	to V+/2.	
Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 7)	Max (Note 6)	Units	
V _{OS}	Input Offset Voltage			±0.2	±3 ±3.8	mV	
TC V _{OS}	Input Offset Voltage Drift	(Note 8)		±0.3	±15	µV/°C	
I _B	Input Bias Current (Note 9)	$V_{CM} = 0.5V$	-1000 -1600	-320		pА	
		V _{CM} = 11.5V		110	800 1900	μΑ	
I _{OS}	Input Offset Current			±10		pА	
CMRR	Common Mode Rejection Ratio	V _{CM} Stepped from 0V to +6V	75 70	115			
		V _{CM} Stepped from 11.4V to 12V	75 68	110		dB	
		V _{CM} Stepped from 0.5V to 11.5	70 65	97			
PSRR	Power Supply Rejection Ratio	$V^{+} = 2.7V$ to 5V, $V_{CM} = 0.5V$	72 68	114			
		$V^+ = 3V$ to 5V, $V_{CM} = 0.5V$	76 72	115		dB	
		$V^{+} = 5V$ to 12V, $V_{CM} = 0.5V$	84 80	117			
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	-0.1 0		12.1 12	V	
A _{VOL}	Large Signal Voltage Gain	Sinking, $V_0 = 0.5V$	89 84	110		dB	
Vo	Output Swing High	Sourcing, $V_0 = 11.5V$ $V_{ID} = 100 \text{ mV}$	11.8	11.85			
.0			11.72			V	
	Output Swing Low	V _{ID} = -100 mV		150	200 280	mV	
I _{SC}	Output Short Circuit Current (Note 10)	Sourcing V _{ID} = 100 mV		-650	-200		
		Sinking V _{ID} = -100 mV	200	1300		μA	
I _S	Supply Current			1.2	1.75 2.5	μA	
SR	Slew Rate (Note 11)	$A_V = +1$, V_O ramped from 1V to 11V	5.25 3.10	7.0		V/ms	
GBW	Gain Bandwidth Product	$R_L = 1 M\Omega, C_L = 50 pF$		25		kHz	
	Phase Margin	$R_L = 1 M\Omega, C_L = 50 pF$		52		deg	
e _n	Input-Referred Voltage Noise	f = 100 Hz		320		nV/√H	
i _n	Input-Referred Current Noise	f = 10 Hz		.02		pA/√H	
		f = 1 kHz		.01		provinz	

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics Tables.

Note 2: Human Body Model: 1.5 k Ω in series with 100 pF. Machine Model: 0 Ω in series with 200 pF.

Note 3: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A)/|\theta_{JA}|$. All numbers apply for packages soldered directly onto a PC board.

Note 4: Output short circuit duration is infinite for V+ < 6V at room temperature and below. For V+ > 6V, allowable short circuit duration is 1.5 ms.

Note 5: Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.

Note 6: Limits are 100% production tested at 25°C. Limits over the operating temperature range are guaranteed through correlations using the Statistical Quality Control (SQC) method.

Note 7: Typical values represent the most likely parametric norm at the time of characterization.

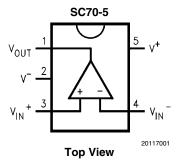
Note 8: Offset voltage drift is guaranteed by design and/or characterization and is not tested in production. Offset voltage drift is determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.

Note 9: Positive current corresponds to current flowing into the device.

Note 10: The Short Circuit Test is a momentary test. See (Note 4).

Note 11: Slew rate is the average of the rising and falling slew rates.

Connection Diagram

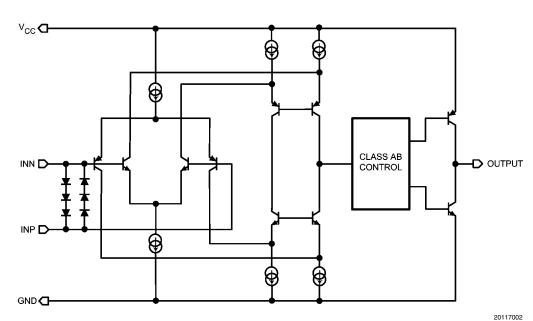


Ordering Information

Package	Part Number	Package Marking	Transport Media	NSC Drawing
5-Pin SC70	LPV511MG	401	1k Units Tape and Reel	
	LPV511MGX	A91 -	A91	3k Units Tape and Reel

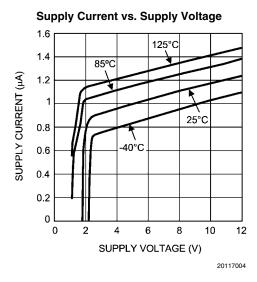
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Simplified Schematic

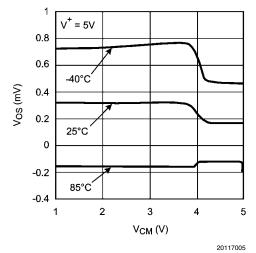


Typical Performance Characteristics At $T_J = 25^{\circ}C$, unless otherwise specified.

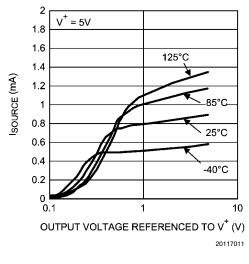
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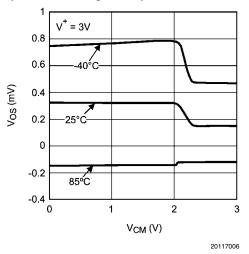
Input Offset Voltage vs. Input Common Mode



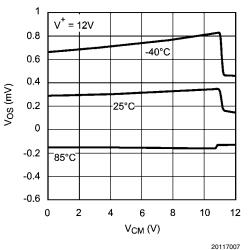


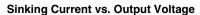


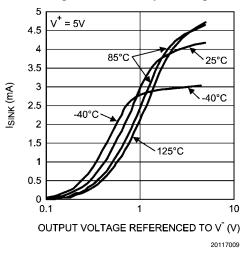
Input Offset Voltage vs. Input Common Mode

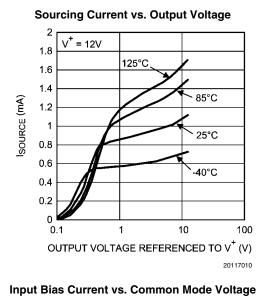


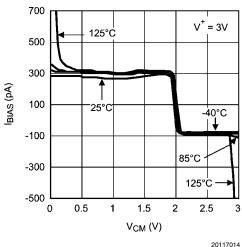
Input Offset Voltage vs. Input Common Mode



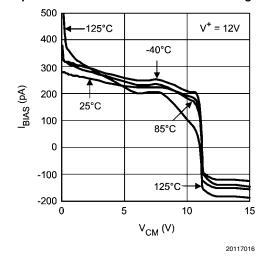




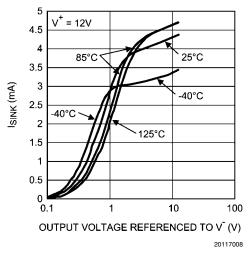




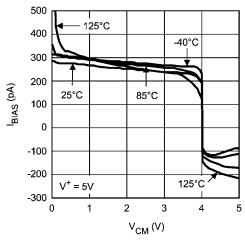
Input Bias Current vs. Common Mode Voltage



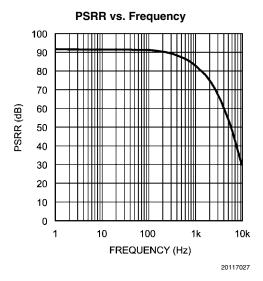
Sinking Current vs. Output Voltage

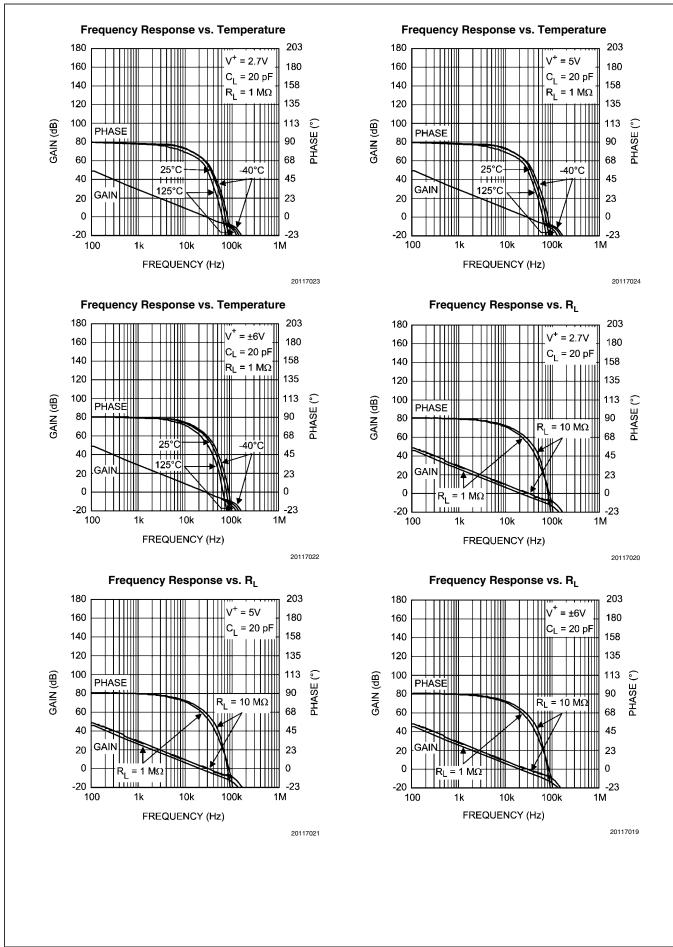


Input Bias Current vs. Common Mode Voltage



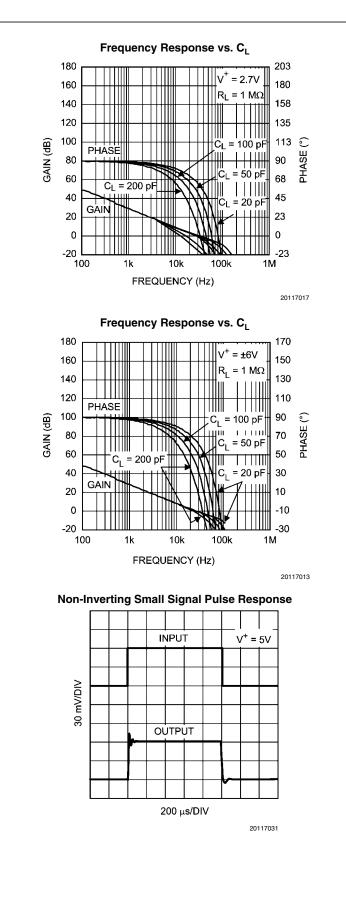
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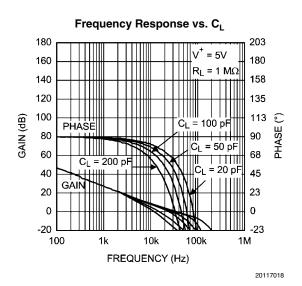




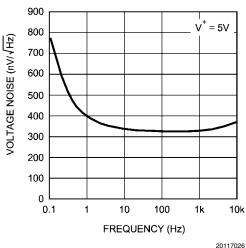
LPV511





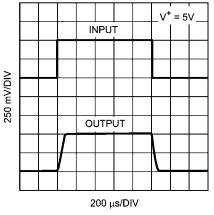


Voltage Noise vs. Frequency



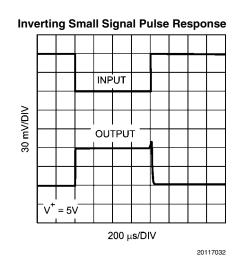
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Non-Inverting Large Signal Pulse Response



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Application Notes

The LPV511 is fabricated with National Semiconductor's state-of-the-art VIP50C process.

INPUT STAGE

The LPV511 has a rail-to-rail input which provides more flexibility for the system designer. As can be seen from the simplified schematic, rail-to-rail input is achieved by using in parallel, one PNP differential pair and one NPN differential pair. When the common mode input voltage (V_{CM}) is near V +, the NPN pair is on and the PNP pair is off. When V_{CM} is near V⁻, the NPN pair is off and the PNP pair is on. When V_{CM} is between V+ and V-, internal logic decides how much current each differential pair will get. This special logic ensures stable and low distortion amplifier operation within the entire common mode voltage range.

Because both input stages have their own offset voltage (V_{OS}) characteristic, the offset voltage of the LPV511 becomes a function of V_{CM}. V_{OS} has a crossover point at 1.0V below V⁺. Refer to the 'V_{OS} vs. V_{CM}' curve in the Typical Performance Characteristics section. Caution should be taken in situations where the input signal amplitude is comparable to the V_{OS} value and/or the design requires high accuracy. In these situations, it is necessary for the input signal to avoid the crossover point.

The input bias current, $\rm I_B$ will change in value and polarity as the input crosses the transition region. In addition, parameters such as PSRR and CMRR which involve the input offset voltage will also be affected by changes in $\rm V_{CM}$ across the differential pair transition region.

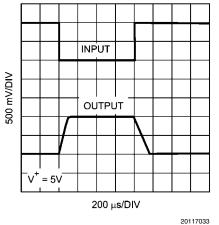
Differential input voltage is the difference in voltage between the non-inverting (+) input and the inverting input (–) of the op amp. Due to the three series diodes across the two inputs, the absolute maximum differential input voltage is ± 2.1 V. This may not be a problem to most conventional op amp designs; however, designers should avoid using the LPV511 as a comparator.

OUTPUT STAGE

The LPV511 output voltage swing 100 mV from rails @ 3V supply, which provides the maximum possible dynamic range at the output. This is particularly important when operating on low supply voltages.

The LPV511 Maximum Output Voltage Swing defines the maximum swing possible under a particular output load. The

Inverting Large Signal Pulse Response



LPV511 output swings 110 mV from the rail @ 5V supply with an output load of 100 $k\Omega.$

DRIVING CAPACITIVE LOAD

The LPV511 is internally compensated for stable unity gain operation, with a 27 kHz typical gain bandwidth. However, the unity gain follower is the most sensitive configuration to capacitive load. Direct capacitive loading reduces the phase margin of the op amp. When the output is required to drive a large capacitive load, greater than 100 pF, a small series resistor at the output of the amplifier improves the phase margin (see *Figure 1*).

In *Figure 1*, the isolation resistor $\rm R_{ISO}$ and the load capacitor $\rm C_L$ form a pole to increase stability by adding more phase margin to the overall system. The desired performance depends on the value of $\rm R_{ISO}$. The bigger the $\rm R_{ISO}$ resistor value, the more stable $\rm V_{OUT}$ will be. But the DC accuracy is degraded when the $\rm R_{ISO}$ gets bigger. If there were a load resistor in *Figure 1*, the output voltage would be divided by $\rm R_{ISO}$ and the load resistor.

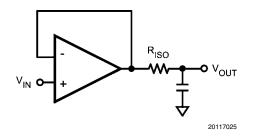


FIGURE 1. Resistive Isolation of Capacitive Load

POWER SUPPLIES AND LAYOUT

The LPV511 operates from a single 2.7V to 12V power supply. It is recommended to bypass the power supplies with a 0.1 μ F ceramic capacitor placed close to the V⁺ and V⁻ pins. Ground layout improves performance by decreasing the amount of stray capacitance and noise at the op amp's inputs and outputs. To decrease stray capacitance, minimize PC board trace lengths and resistor leads, and place external components close to the op amps's pins.

Typical Applications

BATTERY CURRENT SENSING

The rail-to-rail common mode input range and the very low quiescent current make the LPV511 ideal to use in high side and low side battery current sensing applications. The high side current sensing circuit in *Figure 2* is commonly used in a battery charger to monitor the charging current in order to prevent over charging. A sense resistor R_{SENSE} is connected to the battery directly.

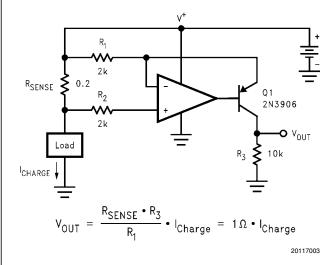


FIGURE 2. High Side Current Sensing

SUMMING AMPLIFIER

The LPV511 operational amplifier is a perfect fit in a summing amplifier circuit because of the rail-to-rail input and output and the sub-micro Amp quiescent current. In this configuration, the amplifier outputs the sum of the three input voltages. The ratio of the sum and the output voltage is defined using feedback and input resistors.

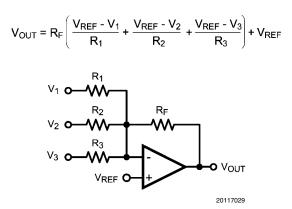
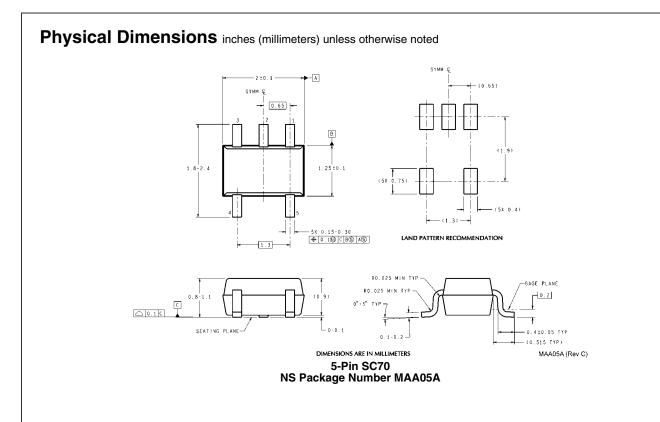


FIGURE 3. Summing Amplifier Circuit



LPV511

Notes

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